











SN74LVC2G34

SCES359J-AUGUST 2001-REVISED OCTOBER 2015

SN74LVC2G34 Dual Buffer Gate

Features

- Available in the Texas Instruments NanoFree™ Package
- Supports 5.5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Maximum t_{pd} of 4.1 ns at 3.3 V
- Low Power Consumption, 10-µA Maximum I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) $<0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Maximum of 5.5 V Down to the V_{CC}
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- **AV Receivers**
- Audio Docks: Portable
- Blu-ray Player and Home Theaters
- **DVD Recorders and Players**
- Embedded PCs
- MP3 Players and Recorders (Portable Audio)
- Personal Digital Assistant (PDA)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid-State Drive (SSD): Client and Enterprise
- TV: LCD/Digital and High-Definition (HDTV)
- Tablets: Enterprise
- Video Analytics: Servers
- Wireless Headsets, Keyboards, and Mice

3 Description

The SN74LVC2G34 device is a dual buffer gate designed for 1.65-V to 5.5-V V_{CC} operation. The SN74LVC2G34 device performs the Boolean function Y = A in positive logic.

NanoFree package technology is breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC2G34DBV	SOT-23 (6)	2.90 mm × 1.60 mm		
SN74LVC2G34DCK	SC70 (6)	2.00 mm × 1.25 mm		
SN74LVC2G34DRL	SOT (6)	1.60 mm × 1.20 mm		
SN74LVC2G34YZP	DSBGA (6)	1.41 mm × 0.91 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic

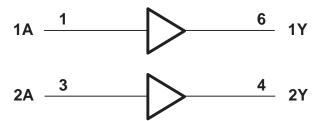




Table of Contents

1	Features 1		8.2 Functional Block Diagram	5
•			8.3 Feature Description	
2	Applications 1			
3	Description 1		8.4 Device Functional Modes	
4	Revision History2	9	Application and Implementation	9
5	Pin Configuration and Functions3		9.1 Application Information	9
_	_		9.2 Typical Application	9
6	Specifications	10	Power Supply Recommendations	
	6.1 Absolute Maximum Ratings	11	Layout	
	6.2 ESD Ratings4	• • •		
	6.3 Recommended Operating Conditions 4		11.1 Layout Guidelines	
	6.4 Thermal Information 4		11.2 Layout Example	10
	6.5 Electrical Characteristics5	12	Device and Documentation Support	<mark>1</mark> 1
	6.6 Switching Characteristics		12.1 Documentation Support	1 1
	6.7 Operating Characteristics		12.2 Community Resources	1 1
	6.8 Typical Characteristics		12.3 Trademarks	<mark>1</mark> 1
7	Parameter Measurement Information 7		12.4 Electrostatic Discharge Caution	<mark>1</mark> 1
8			12.5 Glossary	11
0	Detailed Description 8	13	Mechanical, Packaging, and Orderable	
	8.1 Overview 8	13	Information	11
				! !

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision I (December 2013) to Revision J

Page

- Added Applications, Device Information table, Pin Configuration and Functions section, ESD Ratings table, Thermal Information table, Typical Characteristics section, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section
- Deleted part number from Switching Characteristics table headers.

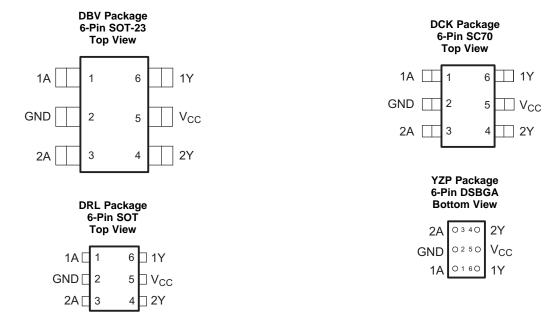
Changes from Revision H (February 2007) to Revision I

Page

Updated document to new TI data sheet format.
 Removed Ordering Information table.
 Updated Features section



5 Pin Configuration and Functions



Pin Functions⁽¹⁾

PIN		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
1A	1	I	Buffer Input 1
1Y	6	0	Buffer Output 1
2A	3	1	Buffer Input 2
2Y	4	0	Buffer Output 2
GND	2	_	Ground pin
V _{CC}	5	_	Power pin

⁽¹⁾ See mechanical drawings for dimensions.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage			6.5	٧
V_{I}	Input voltage ⁽²⁾		-0.5	6.5	٧
Vo	Voltage applied to any output in the high-	impedance or power-off state (2)	-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state (2)(3)		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V ₁ < 0		- 50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current	•		±50	mA
	Continuous current through V_{CC} or GND			±100	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Copyright © 2001–2015, Texas Instruments Incorporated

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.



6.2 ESD Ratings

			VALUE	UNIT
	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	2500	V
V _(ESD)	(ESD) discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
\/	Complement	Operating	1.65	5.5	V
V_{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
.,	High level input valtage	V _{CC} = 2.3 V to 2.7 V	1.7		
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
V	Laurianal innuturaltana	V _{CC} = 2.3 V to 2.7 V		0.7	
V _{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
V_{I}	Input voltage		0	5.5	V
V_{O}	Output voltage		0	V_{CC}	V
	High-level output current	V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
I_{OH}		V _{CC} = 3 V		-16	mA
		V _{CC} = 3 V		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V 2V		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
		V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5	
_	Operating free pir temperature	DBV, DCK, DRL Package	-40	125	°C
T_A	Operating free-air temperature	YZP Package	-40	85	-0

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Semiconductor and Implications of Slow or Floating CMOS Inputs, SCBA004.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G34				
		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	YZP (DSBGA)	UNIT
		6 PINS	6 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	165	259	142	123	°C/W

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	R TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾	MAX	UNIT	
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1				
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			.,	
V _{OH}	$I_{OH} = -16 \text{ mA}$	2.1/	2.4			V	
	$I_{OH} = -24 \text{ mA}$	3 V	2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8				
	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1		
	I _{OL} = 4 mA	1.65 V			0.45		
	I _{OL} = 8 mA	2.3 V			0.3	V	
V _{OL}	I _{OL} = 16 mA	3 V			0.4	V	
	I _{OL} = 24 mA	3 V			0.55		
	I _{OL} = 32 mA	4.5 V			0.55		
I _I A input	s V _I = 5.5 V or GND	0 to 5.5 V			±5	μΑ	
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0			±10	μΑ	
I _{cc}	V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V	1		10	μΑ	
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ	
C _i	V _I = V _{CC} or GND	3.3 V		3.5		pF	

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OPERATING FREE-AIR TEMPERATURE (T _A)	V _{cc}	MIN	MAX	UNIT
			\	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.2	8.6	
	Α	Y		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	4.4	
t _{pd}	A	Ť	−40°C to 85°C	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4	4.1	ns
				$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	1	3.2	
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.2	9.6		
	٨	A Y	–40°C to 125°C	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	4.9	
t _{pd}	A			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	4.6	ns
					V _{CC} = 5 V ± 0.5 V	1	3.7

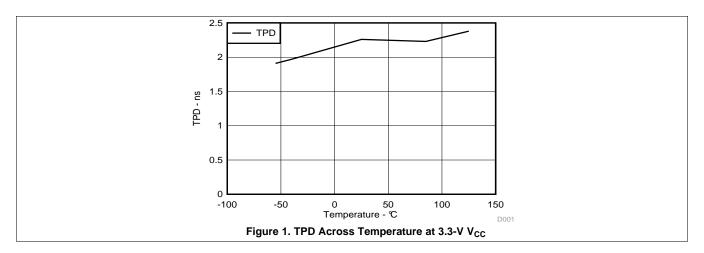
6.7 Operating Characteristics

 $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC}	TYP	UNIT
C _{pd} Power			V _{CC} = 1.8 V	14	
	Power dissipation capacitance	f = 10 MHz	V _{CC} = 2.5 V	14	~F
			V _{CC} = 3.3 V	15	pF
			V _{CC} = 5 V	17	

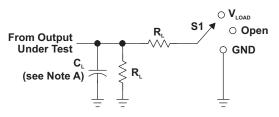


6.8 Typical Characteristics





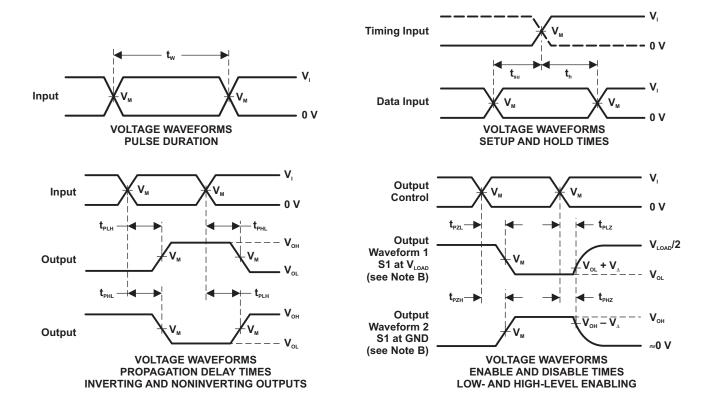
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INI	PUTS		.,			.,
V _{cc}	V _i	t,/t,	V _M	V _{LOAD}	C _L	R _∟	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
$2.5~V~\pm~0.2~V$	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
$3.3~V\pm0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

Submit Documentation Feedback

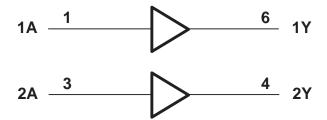


8 Detailed Description

8.1 Overview

The SN74LVC2G34 device contains two buffer gates that each perform the Boolean function Y = A. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74LVC2G34 device has a wider operating voltage range, operating from 1.65 V to 5.5 V, and allows down voltage translation. The SN74LVC2G34 $I_{\rm off}$ feature allows voltages on the inputs and outputs when $V_{\rm CC}$ is 0 V.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G34.

Table 1. Function Table

INPUT A	OUTPUT Y
Н	Н
L	Ĺ

Submit Documentation Feedback



9 Application and Implementation

9.1 Application Information

The SN74LVC2G34 is a high-drive CMOS device that can be used as a buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V, making it ideal for driving multiple outputs and good for high-speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to $V_{\rm CC}$.

9.2 Typical Application

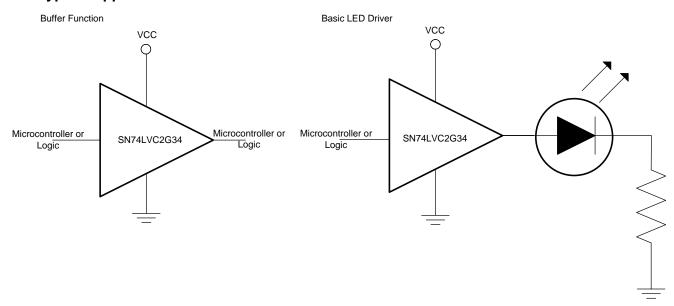


Figure 3. Typical Application

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions must be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- Recommended Input Conditions
 - Rise time and fall time specs. See $(\Delta t/\Delta V)$ in the *Recommended Operating Conditions* table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (VI max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

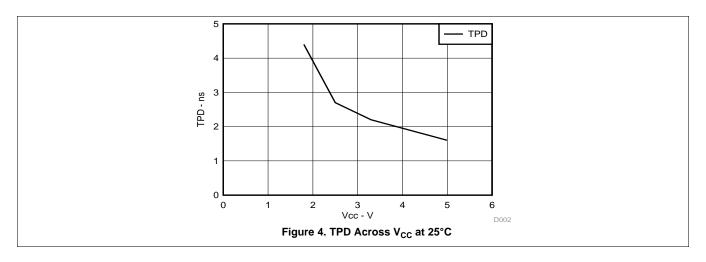
2. Recommended Output Conditions

- Load currents must not exceed (I_O max) per output and must not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the Recommended Operating Conditions table.
- Outputs much not be pulled above V_{CC} under normal operating conditions.



Typical Application (continued)

9.2.3 Application Curve



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F capacitor is recommended and if there are multiple V_{CC} pins then a 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever make more sense or is more convenient.

11.2 Layout Example





12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Documentation Support

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

www.ti.com 30-Jun-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC2G34DBVR	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34K, C34O, C34R)
SN74LVC2G34DBVR.B	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34K, C34O, C34R)
SN74LVC2G34DBVRE4	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C34F, C34R)
SN74LVC2G34DBVRG4	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C34F, C34R)
SN74LVC2G34DBVRG4.B	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C34F, C34R)
SN74LVC2G34DBVT	Active	Production	SOT-23 (DBV) 6	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34K, C34R)
SN74LVC2G34DBVT.B	Active	Production	SOT-23 (DBV) 6	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34K, C34R)
SN74LVC2G34DBVTG4	Active	Production	SOT-23 (DBV) 6	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C34F, C34R)
SN74LVC2G34DBVTG4.B	Active	Production	SOT-23 (DBV) 6	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C34F, C34R)
SN74LVC2G34DCK3	Last Time Buy	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SNBI	Level-1-260C-UNLIM	-40 to 85	C9Z
SN74LVC2G34DCK3.B	Last Time Buy	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SNBI	Level-1-260C-UNLIM	-40 to 85	C9Z
SN74LVC2G34DCKR	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C95, C9F, C9K, C9 R)
SN74LVC2G34DCKR.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(C95, C9F, C9K, C9 R)
SN74LVC2G34DCKRE4	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95
SN74LVC2G34DCKRG4	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95
SN74LVC2G34DCKRG4.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95
SN74LVC2G34DRLR	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(1K8, C97, C9R)
SN74LVC2G34DRLR.B	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(1K8, C97, C9R)
SN74LVC2G34DRLRG4	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1K8
SN74LVC2G34DRLRG4.B	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1K8
SN74LVC2G34YZPR	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9N
SN74LVC2G34YZPR.B	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9N

⁽¹⁾ Status: For more details on status, see our product life cycle.

PACKAGE OPTION ADDENDUM

www.ti.com 30-Jun-2025

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC2G34:

Enhanced Product : SN74LVC2G34-EP

NOTE: Qualified Version Definitions:

Enhanced Product - Supports Defense, Aerospace and Medical Applications



www.ti.com 13-Aug-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G34DBVR	SOT-23	DBV	6	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC2G34DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC2G34DBVRG4	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G34DBVT	SOT-23	DBV	6	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G34DBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G34DBVTG4	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G34DCKR	SC70	DCK	6	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC2G34DCKRG4	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G34DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC2G34DRLRG4	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC2G34YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



www.ti.com 13-Aug-2025

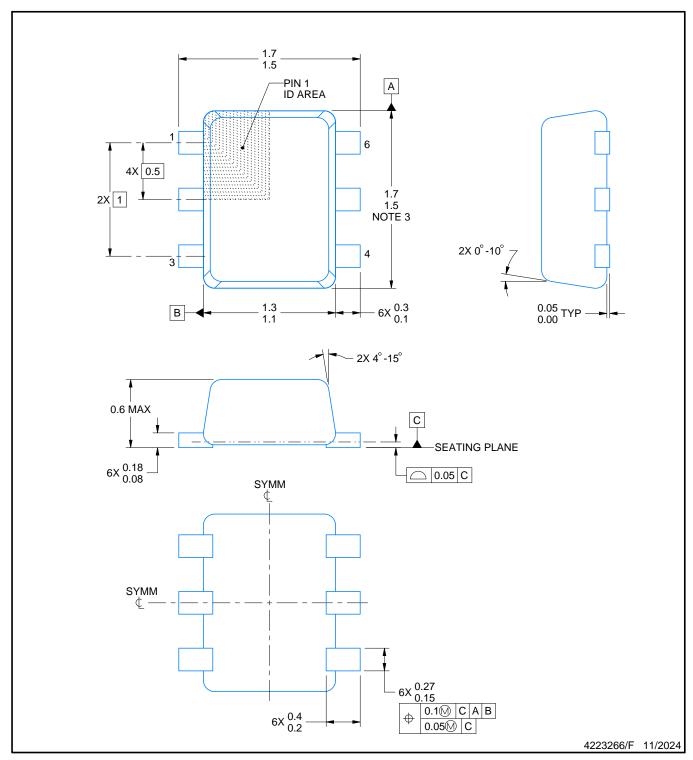


*All dimensions are nominal

7 til dilliciololio ale nominal							To the state of th
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G34DBVR	SOT-23	DBV	6	3000	208.0	191.0	35.0
SN74LVC2G34DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
SN74LVC2G34DBVRG4	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G34DBVT	SOT-23	DBV	6	250	202.0	201.0	28.0
SN74LVC2G34DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
SN74LVC2G34DBVTG4	SOT-23	DBV	6	250	180.0	180.0	18.0
SN74LVC2G34DCKR	SC70	DCK	6	3000	210.0	185.0	35.0
SN74LVC2G34DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G34DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0
SN74LVC2G34DRLRG4	SOT-5X3	DRL	6	4000	210.0	185.0	35.0
SN74LVC2G34YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



PLASTIC SMALL OUTLINE



NOTES:

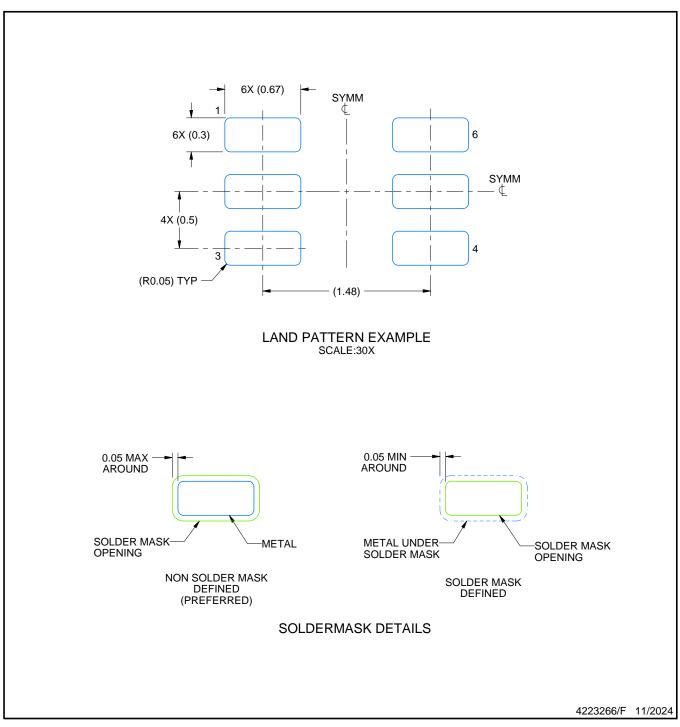
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD



PLASTIC SMALL OUTLINE

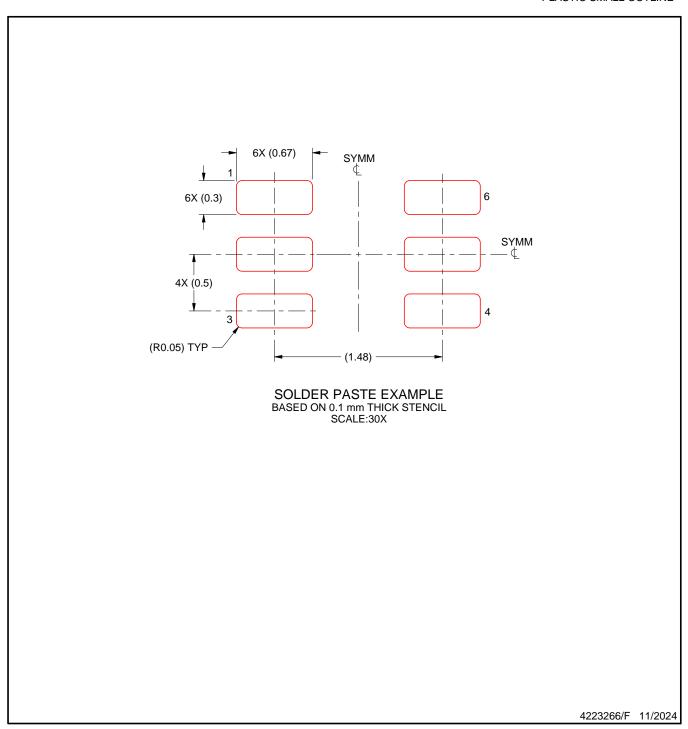


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

 4. Falls within JEDEC MO-203 variation AB.





NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated